



RF ESD Protection Diodes

- ESD protection of RF antenna / interfaces or ultra high speed data lines acc. to: IEC61000-4-2 (ESD): ± 20 kV (air / contact) IEC61000-4-4 (EFT): 40 A (5/50 ns) IEC61000-4-5 (surge): 10 A (8/20 μs)
- Very low line capacitance: 0.8 pF @ 1 GHz (0.4 pF per diode)
- Ultra low series inductance: 0.4 nH per diode
- Very low clamping voltage
- Ultra small leadless package 1.2 x 0.8 x 0.39 mm
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

Applications in anti-parallel configuration

 For low RF signal levels without superimposed DC voltage: e.g. GPS, XM-Radio, Sirius, DVB, DMB, DAB, Remote Keyless Entry

Applications in rail-to-rail configuration

- For high RF signal levels or low RF signal levels with superimposed DC voltage: e.g. HDMI, S-ATA, Gbit Ethernet
- For more technical details on ESD and Antenna protection please refer to Application Note No.103 on www.infineon.com/tvsdiodes



ESD0P8RFL



Туре	Package	Configuration	Marking
ESD0P8RFL	TSLP-4-7	anti-parallel	E8





Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit				
ESD contact discharge ¹⁾	V _{ESD}	20	kV				
Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾	I _{pp}	10	A				
Operating temperature range	T _{op}	-55150	°C				
Storage temperature	T _{stg}	-65150					

Electrical Characteristics at $T_A = 25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics -		•	•	•	•
Reverse working voltage ³⁾	V _{RWM}	-	-	50	V
Reverse current ³⁾	I _R	-	-	100	nA
<i>V</i> _R = 50 V					
Forward clamping voltage ²⁾	V _{FC}	-	12	15	V
<i>I</i> _{PP} = 10 A					
Line capacitance ⁴⁾	CT	-	0.8	-	pF
<i>V</i> _R = 0 V, <i>f</i> = 1 GHz					
Series inductance (per diode)	LS	-	0.4	-	nH

¹V_{ESD} according to IEC61000-4-2, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

 $^{2}I_{pp}$ according to IEC61000-4-5, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

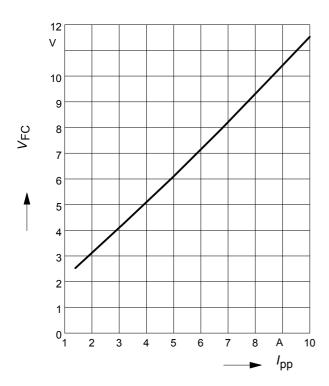
³Only valid in rail-to-rail configuration with $V_{CC} \ge V_{RWM}$

⁴Total capacitance line to ground (2 diodes in parallel)



Forward clamping voltage $V_{FC} = f(I_{PP})$

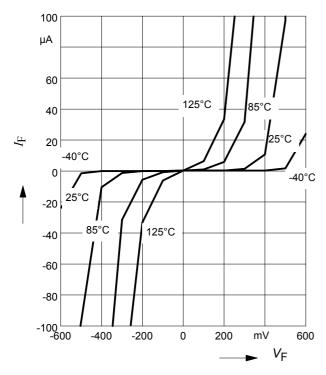
 $t_{\rm p}$ = 8 / 20 µs



Forward current $I_{\rm F}$ = $f(V_{\rm F})$

T_A = Parameter

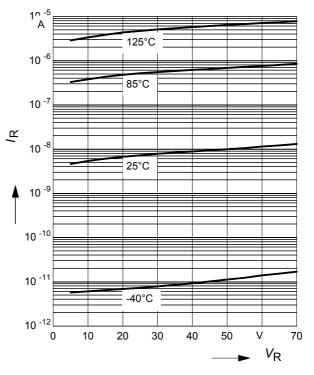
leakage in anti-parallel configuration



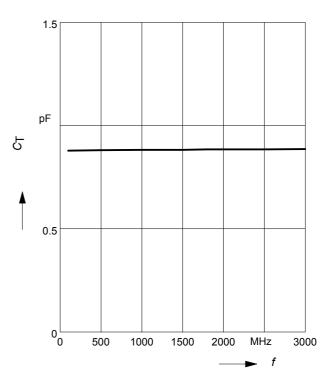
Reverse current $I_{R} = f(V_{R})$

 T_A = Parameter

leakage in rail-to-rail configuration



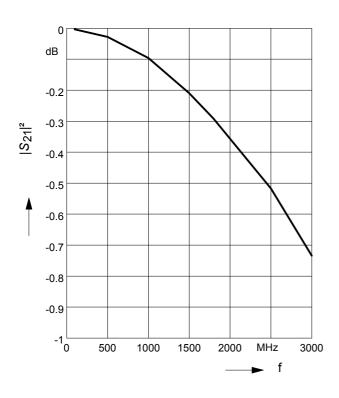
Line capacitance $C_{T} = f$ (f) $V_{R} = 0 V$







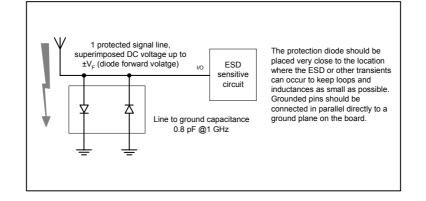
$Insertion \ loss \ l_L = -|S_{21}|^2 = f(f) \\ V_{\mathsf{R}} = 0 \ \mathsf{V}, \ Z = 50 \ \Omega$





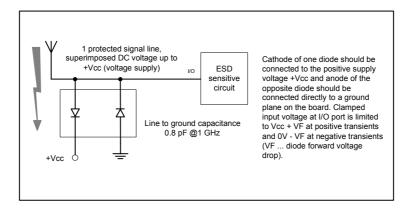
1. Application example

1 RF signal channel, anti-parallel configuration, please refer also to Application Note No.103

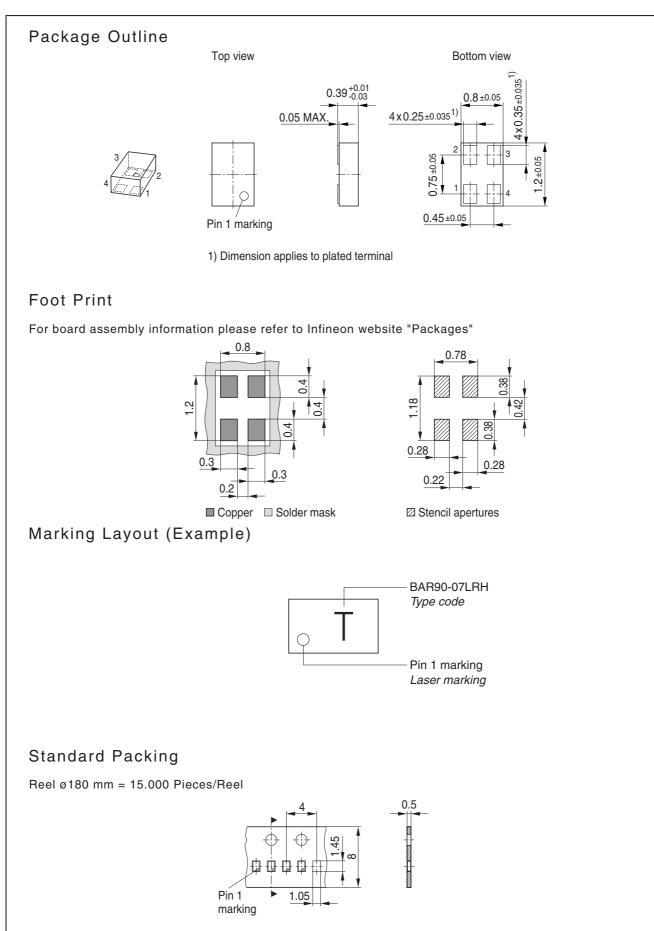


2. Application example

1 RF signal channel, rail-to-rail configuration









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